

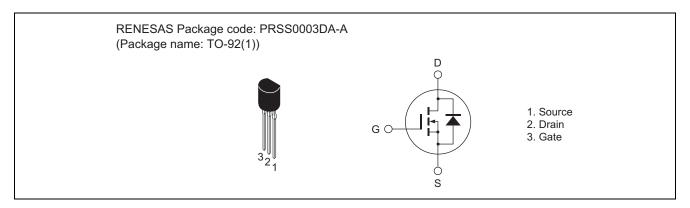
# RJK6011DJA

600V - 0.1A - MOS FET High Speed Power Switching R07DS0873EJ0200 Rev.2.00 Jan 28, 2014

### **Features**

- Low on-resistance  $R_{DS(on)} = 35~\Omega~typ.~(at~I_D=0.05~A,~V_{GS}=10~V,~Ta=25^{\circ}C)$
- Low drive current
- High density mounting

### **Outline**



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

| Item  | Symbol                        | Ratings     | Unit |
|---|-------------------------------|-------------|------|
| Drain to source voltage                     | V <sub>DSS</sub>              | 600         | V    |
| Gate to source voltage                      | V <sub>GSS</sub>              | ±30         | V    |
| Drain current                               | I <sub>D</sub>                | 0.1         | Α    |
| Drain peak current                          | I <sub>D (pulse)</sub> Note1  | 0.4         | А    |
| Body-drain diode reverse drain current      | I <sub>DR</sub>               | 0.1         | Α    |
| Body-drain diode reverse drain peak current | I <sub>DR (pulse)</sub> Note1 | 0.4         | Α    |
| Channel dissipation                         | Pch                           | 0.75        | W    |
| Channel to ambient thermal impedance        | θ <sub>ch-a</sub>             | 166.7       | °C/W |
| Channel temperature                         | Tch                           | 150         | °C   |
| Storage temperature                         | Tstg                          | -55 to +150 | °C   |

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

### **Electrical Characteristics**

 $(Ta = 25^{\circ}C)$ 

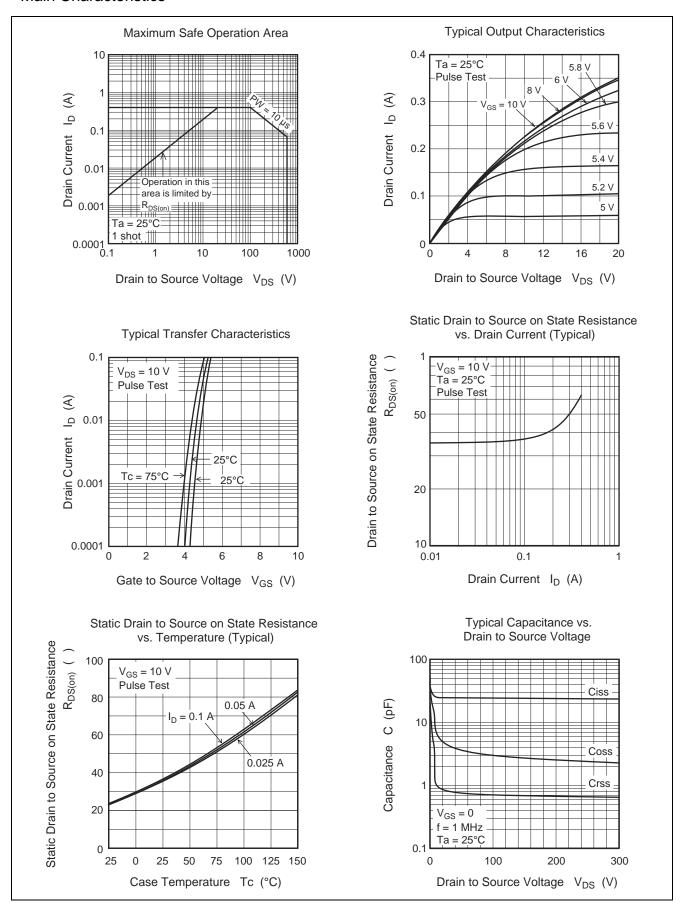
| Item                              | Symbol               | Min | Тур  | Max  | Unit | Test conditions  |
|-----------------------------------|----------------------|-----|------|------|------|--|
| Drain to source breakdown voltage | $V_{(BR)DSS}$        | 600 | _    | _    | V    | $I_D = 10 \text{ mA}, V_{GS} = 0$                            |
| Zero gate voltage drain current   | I <sub>DSS</sub>     | _   | _    | 1    | μΑ   | $V_{DS} = 600 \text{ V}, V_{GS} = 0$                         |
| Gate to source leak current       | I <sub>GSS</sub>     |     | _    | ±0.1 | μΑ   | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$                      |
| Gate to source cutoff voltage     | V <sub>GS(off)</sub> | 3   | _    | 5    | V    | $V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$                |
| Static drain to source on state   | R <sub>DS(on)</sub>  | _   | 35   | 52   | Ω    | $I_D = 0.05 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note2}}$ |
| resistance                        |                      |     |      |      |      |  |
| Input capacitance                 | Ciss                 |     | 25   |      | pF   | V <sub>DS</sub> = 25 V                                       |
| Output capacitance                | Coss                 |     | 4.7  | _    | pF   | $V_{GS} = 0$   |
| Reverse transfer capacitance      | Crss                 | _   | 0.9  | _    | pF   | f = 1 MHz  |
| Turn-on delay time                | t <sub>d(on)</sub>   | _   | 33   | _    | ns   | $I_D = 0.05 A$   |
| Rise time                         | t <sub>r</sub>       | _   | 16   | _    | ns   | V <sub>GS</sub> = 10 V                                       |
| Turn-off delay time               | t <sub>d(off)</sub>  | _   | 54   | _    | ns   | $R_L = 6000 \Omega$  |
| Fall time                         | t <sub>f</sub>       | _   | 300  | _    | ns   | $Rg = 10 \Omega$   |
| Total gate charge                 | Qg                   | _   | 3.7  | _    | nC   | V <sub>DD</sub> = 480 V                                      |
| Gate to source charge             | Qgs                  | _   | 0.4  | _    | nC   | V <sub>GS</sub> = 10 V                                       |
| Gate to drain charge              | Qgd                  | _   | 2.7  | _    | nC   | $I_D = 0.1 A$  |
| Body-drain diode forward voltage  | $V_{DF}$             | _   | 0.80 | 1.35 | V    | $I_F = 0.1 \text{ A}, V_{GS} = 0^{\text{Note2}}$             |

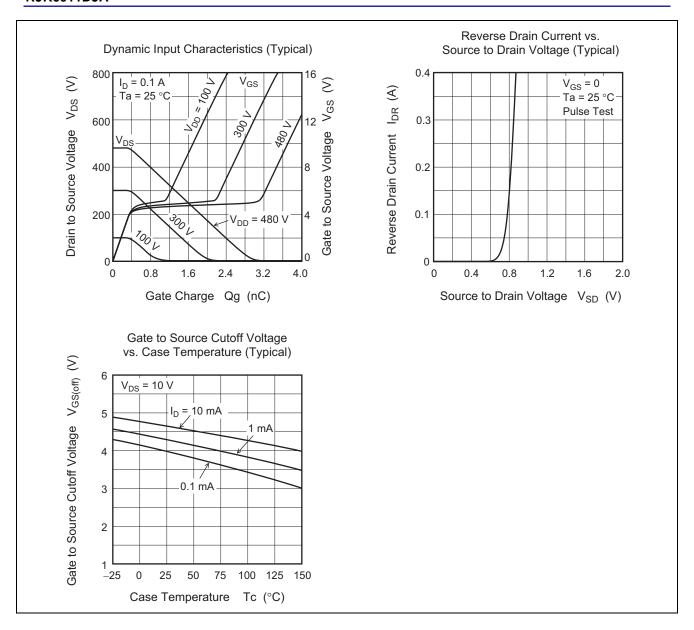
Notes: 2. Pulse test

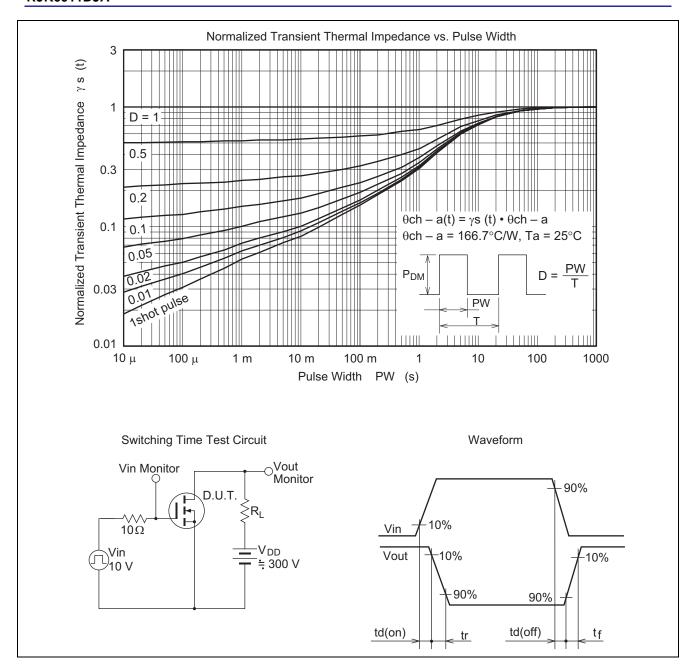
- 3. Since this device is equipped with high voltage FET chip ( $V_{DSS} \ge 600 \text{ V}$ ), high voltage may be supplied. Therefore, please be sure to confirm about Electric discharge between Drain terminal and other terminal.
- 4. This device is sensitive to electrostatic discharge.

  It is recommended to adopt appropriate cautions when handling this product.

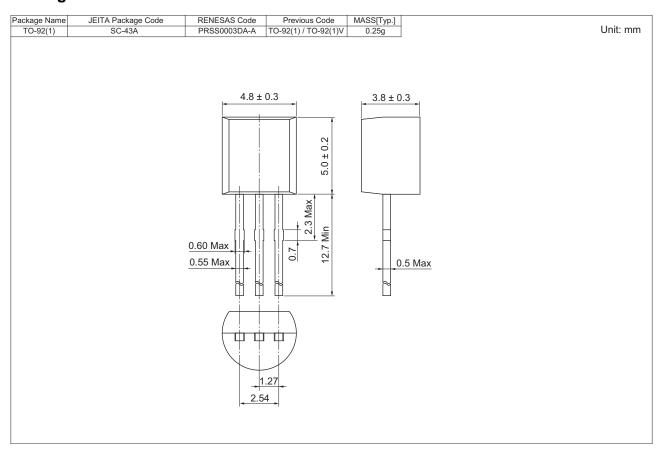
### Main Characteristics







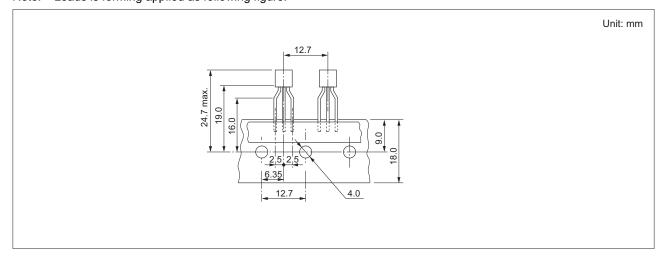
# **Package Dimensions**



# **Ordering Information**

| Orderable Part Number | Quantity | Shipping Container      |
|-----------------------|----------|-------------------------|
| RJK6011DJA-00#Z0      | 2500 pcs | Hold Box, Radial Taping |

Note: Leads is forming applied as following figure.



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